

# PIN Diodes

**Q:** *Just how do we **make switches and voltage controlled attenuators?***

**A:** Typically, they are constructed with **PIN diodes**.

A PIN diode is simply a  $p-n$  junction diode that is designed to have a very **small junction capacitance** (0.01 to 0.1 pf).

→ Sort of the **opposite** of the **varactor diode!**

To see why this is important, recall diode **small signal analysis** from your first electronics course.

In small signal analysis, the **total** diode voltage consists of a **D.C. bias voltage** ( $V_D$ ) and a **small, time-varying signal** ( $v_d$ ):

$$v_D(t) = V_D + v_d(t)$$

For radio engineering applications, the small signal is a **microwave signal** !!! I.E.,:

$$v_D(t) = V_D + v_{RF}(t)$$

Thus, we know that the **diode current**  $i_D$  is:

$$i_D = I_s \left( \exp \left[ \frac{V_D + v_{RF}(t)}{nV_T} \right] - 1 \right)$$

Since  $v_{RF}$  is very **small**, we can **approximate** this diode current  $i_D(v_D)$  using a **Taylor Series** expansion around  $v_D = V_D$ :

$$\begin{aligned} i_D(v_D) &\approx i_D(v_D)\Big|_{v_D=V_D} + \frac{\partial i_D(v_D)}{\partial v_D}\Big|_{v_D=V_D} v_{RF}(t) \\ &= I_S \left( e^{v_D/nV_T} - 1 \right) + \frac{I_S e^{v_D/nV_T}}{nV_T} v_{RF}(t) \end{aligned}$$

We recognize that:

$$I_S \left( e^{v_D/nV_T} - 1 \right) = \text{D.C. Bias Current} \doteq I_D$$

and thus we can write our **small-signal approximation** as:

$$\begin{aligned} i_D &= I_D + \frac{(I_D + I_S)}{nV_T} v_{RF}(t) \\ &= I_D + \frac{v_{RF}(t)}{r_d} \end{aligned}$$

where we have defined the diode **small-signal resistance**  $r_d$  as:

$$r_d = \frac{nV_T}{I_D + I_S}$$

The diode small-signal resistance is also **often** referred to as the **junction** resistance  $R_j$  or the **series** resistance  $R_s$ .

We can further conclude that the total diode current  $i_D$  is the sum of the D.C. bias current  $I_D$ , and the **small-signal current**  $i_{RF}(t)$ , where:

$$i_{RF}(t) = \frac{v_{RF}(t)}{r_d}$$

→ Just like **Ohm's Law** !

To a small (i.e., low power) microwave signal, a diode "looks" like a **resistor**.

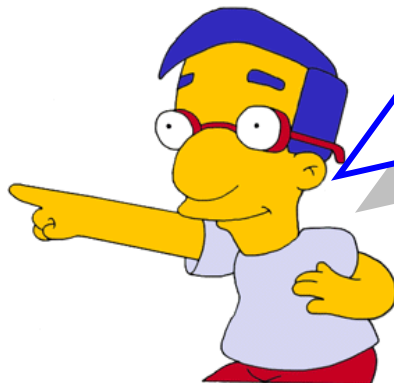
Moreover, we can **control** and **modify** the resistance of the diode by **changing** the D.C. bias.

→ Sort of a **voltage-controlled** resistor!

For example, if we put the diode into **forward** bias ( $V_D \gg nV_T$ ), the bias current  $I_D$  will be positive and **big**, thus the junction resistance will be very **small** (e.g.,  $r_d =$  a few ohms).

→ A **forward** biased diode is very nearly a microwave **short circuit**!

$$r_d = \frac{nV_T}{I_D + I_s}$$



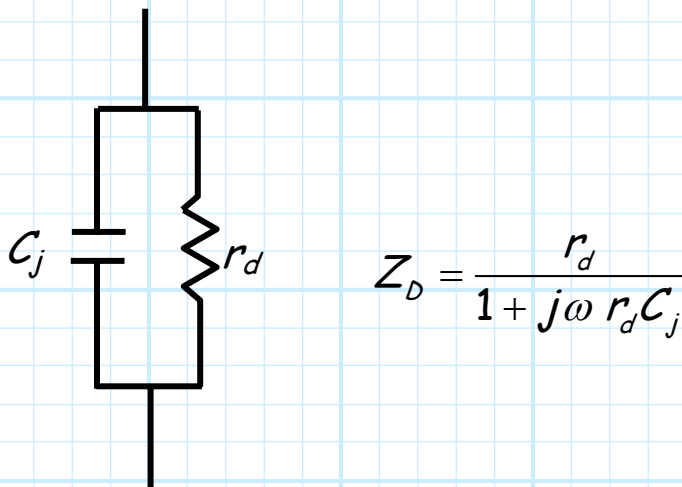
*I get it! If we **reverse** bias our diode, such that  $V_D \ll -nV_T$ , the bias current  $I_D$  will be **nearly** equal to  $-I_s$ . As a result, the **series resistance** will be **hugemungous**!*

Not so fast! The small-signal **resistance** of a **reverse** biased diode is in fact **very large**. BUT, we must also consider the junction **capacitance**  $C_j$ !

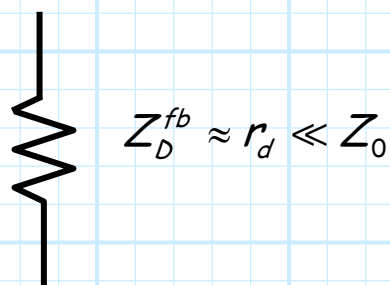


Recall that in **reverse** bias, the junction capacitance of a diode can be **significant**, and in fact generally **increases** as the bias voltage becomes more negative!

As a result, a good microwave circuit **model** of a diode includes both the series resistance and junction capacitance:



For **forward** bias, where  $r_d$  is **very small**, we find that diode impedance  $Z_D$  is approximately equal to this **small series resistance** ( $Z_D \approx r_d$ )—a **short circuit** (approximately):



For reverse bias, where  $r_d$  is **very large**, we find that diode impedance  $Z_D$  is approximately equal to that of the junction capacitance  $C_j$ :

$$Z_D^{rb} = \frac{1}{j\omega C_j} \gg Z_0$$

For low-frequencies (e.g., kHz), this impedance will be typically be **very large** and thus the diode can be approximate as an **open** circuit.

However, at microwave frequencies (where  $\omega$  is very large) the reverse bias impedance  $Z_D^{rb}$  may **not** be particularly large, and thus the reverse biased diode **cannot** be considered an open circuit.

In order for the impedance  $Z_D^{rb} = 1/j\omega C_j$  to be very **large** at **microwave** frequencies, the junction capacitance  $C_j$  must be **very, very small**.



***PIN** diodes! I bet that's why we use **PIN** diodes!*

That's **exactly** why! A PIN diode is **approximately** a (bias) **voltage controlled resistor** at microwave frequencies. We can select any value of  $r_d$  from a **short** to an **open**.

As a result, we can make **many** interesting devices!